

CLEAN COPY OF THE CLAIMS AS AMENDED

*Sub D1*  
1 (Amended). An anisotropic etch mixture for a silicon substrate connected to a low power bias source consisting of one or more of a fluorine-containing gas selected from the group consisting of SF<sub>6</sub>, Si<sub>2</sub>F<sub>6</sub> and SiF<sub>4</sub>, HBr and oxygen.

*B1*  
4 (Amended). An etch mixture for silicon consisting essentially of a fluorine-containing gas that includes SF<sub>6</sub>, Si<sub>2</sub>F<sub>6</sub> and SiF<sub>4</sub> and HBr and oxygen.